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11 7
12a 12f

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14 : 1
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16 :
17 : DM

, , , 가 , 가 (DM) DM (, DM)가 USP5,712,652가 2 , () , DM , DM SRAM SRAM 5 가 DM 1 , 1 2 1 2 , 1 1

Figure 1 is a schematic diagram of a semiconductor device 100. The device 100 includes a substrate 1, a gate insulating layer 2, a gate electrode 3, a channel layer 4, a source/drain layer 5, and a passivation layer 6. The gate electrode 3 is formed on the substrate 1, and the channel layer 4 is formed on the gate electrode 3. The source/drain layer 5 is formed on the channel layer 4, and the passivation layer 6 is formed on the source/drain layer 5. The device 100 is a top-gate type semiconductor device. The gate electrode 3 is formed on the substrate 1, and the channel layer 4 is formed on the gate electrode 3. The source/drain layer 5 is formed on the channel layer 4, and the passivation layer 6 is formed on the source/drain layer 5. The device 100 is a top-gate type semiconductor device.

(15), 2 (21) 3 (22),
 (19b) (13) 3 (22)
 (25), 1 (19a)
 (19a) 2 (21) (13)
 2 (25) 2 (25) (19b) 1
 (13) (23) (15)
 가 4 3 (22)
 2 (21) 2 (21)
 3 (22) 1/10 3 (22)
 High /Low (21) 3 가 (22) 1 (13)
 (15) (10) High (16)
 (10) (16) (16)
 (110) (19) (15)
 (18) 가 1 (24) (13) DM
 Cs
 1 (24)
 4 (19a, 19b) (19b) (120)
 (130) (17) 5 3 (10)
 DM (37) N-chTFT 2 (31) P-chTFT 3
 (32) (19) (31) 3 (32)
 / 가 (32)가 5 2 DM (31)가 (37) 2 (31)가 (32)가
 3 (31) 가 2 (25) 5
 (19) 3 (31) N-chTFT 3 (32) P-chTFT (32) CMOS
 2 (31) 2 (31) 3
 DM (18) 5
 6 5 (10) 6 5
 DM (18) (23) P-chTFT(231) N-chTFT(232)
 28b) P-chTFT(231) (28a) N-chTFT(232)
 (23) 2 (25)
 4) 7 가 7 3 (233) P-chTFT(231) 3 (233) 4 (23)
 (234) N-chTFT(232) (28b)
 (233) 4 (234) (31) 1 (24) 2 (25) 3
 (13)
 DM (18) 3 (25, 233, 234) 1 DM (18) (24)
 3
 가 1 (24)

6

8 (28a, 28b) High, Low

(19) 2 (31)

1 (14)가 (17) 2 (31) (11)

1 (14) DM 가 (18) 2 DM (18) (25)

1 (14)가 DM (18)

(前回) (15)

가 (1)

6) 가 가 (120) (130) (19)

4 DM (18)

가

9 (28a, 28b) (High /Low 가)

8 1 가 , DM (18)

1 (28a, 28b)

(15) 9 6 (31) 3 (23)

(19) (25)

32) 2 (23) P-chTFT(231) N-chTFT(232)

P-chTFT(231) N-chTFT(232) High Low 2

(23) P-chTFT(231) N-chTFT(232) 가 , DM (18)

(13) 가 P-chTFT(231) N-chTFT(232) (27), 3 (32)

(28b) 3 (32) 가 High , N-chTFT(232)

(15) 가 Low 가 (13)

(32) High 가 , P-chTFT(231)가 (28a) 3

(16) (13) 가 (15) 가

(28a, 28b) (13)

(15) 가 (15)

1 (28a, 28b)

1 (24)

10, 11 10 6 (23) 11 7 10

11 1 (24) (29) (28a) (29) (23) (28b)(28a)

(29) 가

가

(100) 12 12a 12f

(110)

1 (120) (1)

) (6)

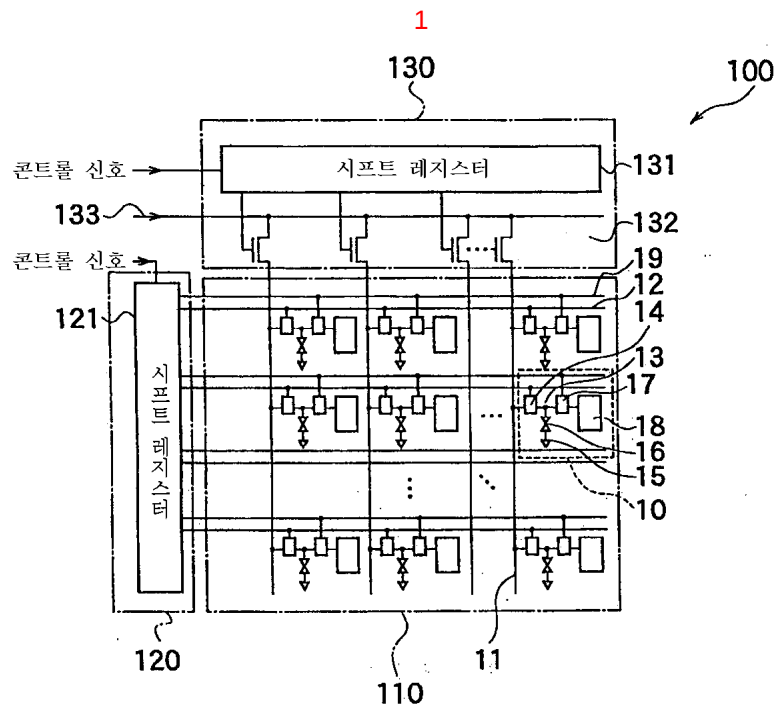
(1) (12a)

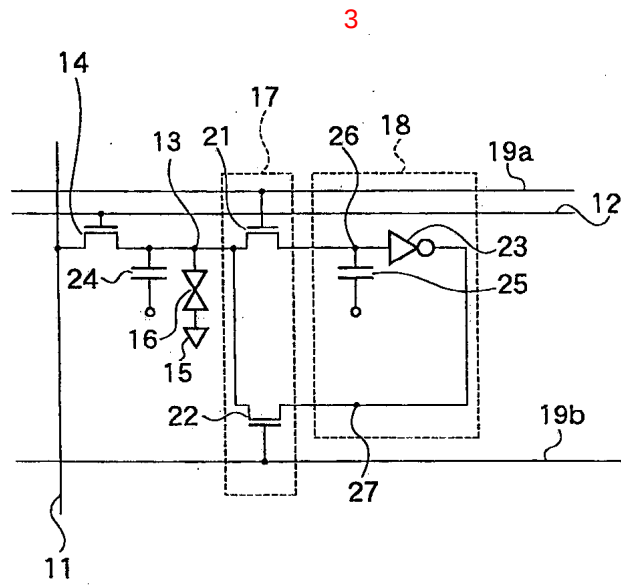
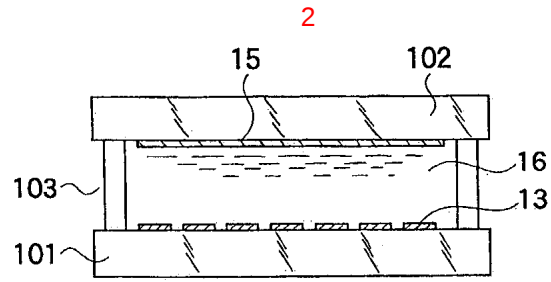
(50) (51) CVD XeCl 50nm (a-Si) (51)

XeCl (52) A (52)

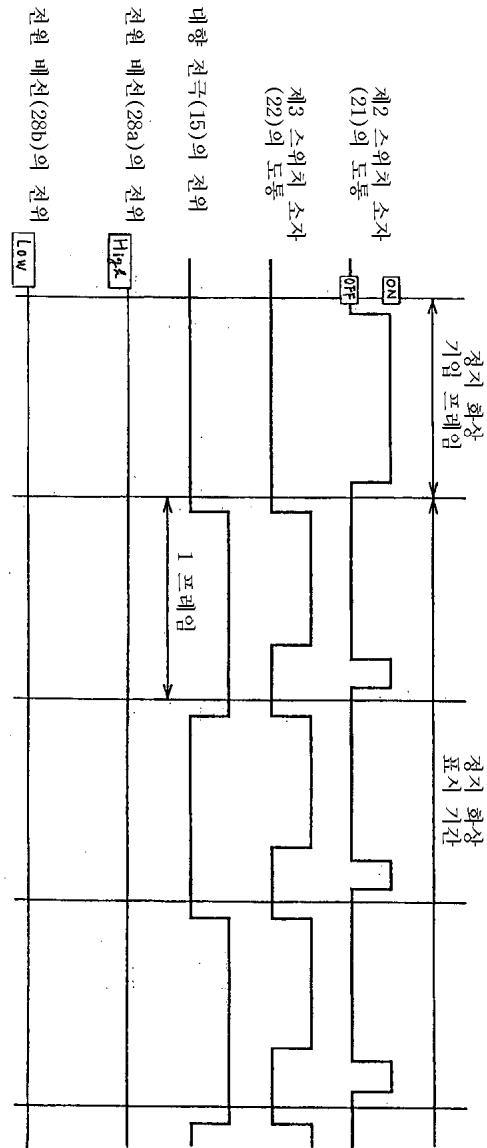
- 1
- 1 1 , ,
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- 3.
- 1 , CMOS .
- 4.
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- 1 , 2 ,
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- 6.
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- 3
- 2 2
- 7.
- 5 , 3 ,
- 2
- 8.
- 5 , 3 ,
- 2
- 9.
- 3 , CMOS , 3 4 가 .
- 10.
- 1 , 1
- 11.
- 1 ,
- 12.
- 1 ,
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- 1 1
- 2 , 1 , 1
- 2 , 2 , 1
- 2
- 13.
- 12 , 2
- 1 ,
- 14.
- 12 ,

- 2, 1 2 3, 2
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20. 16, 16

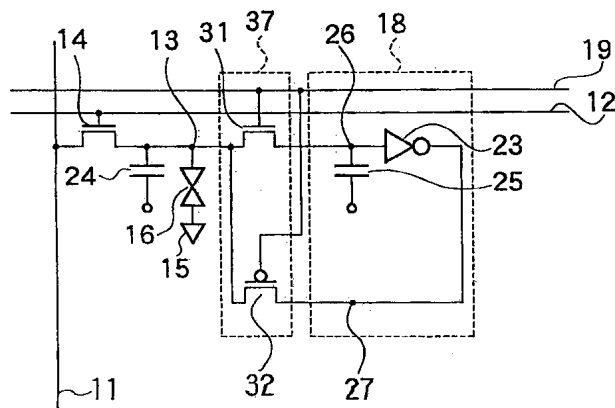




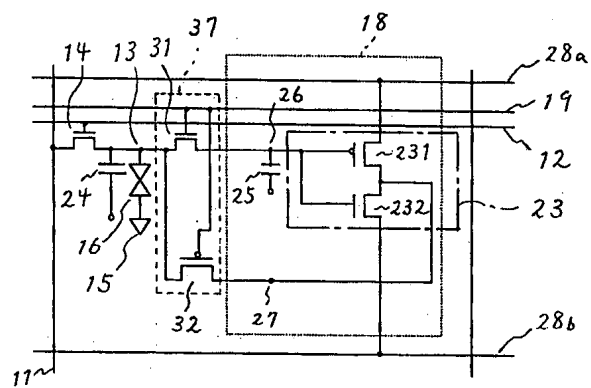
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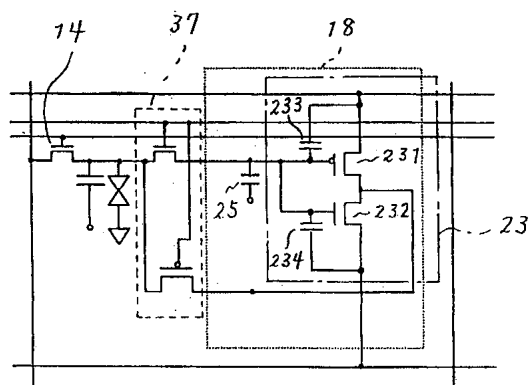
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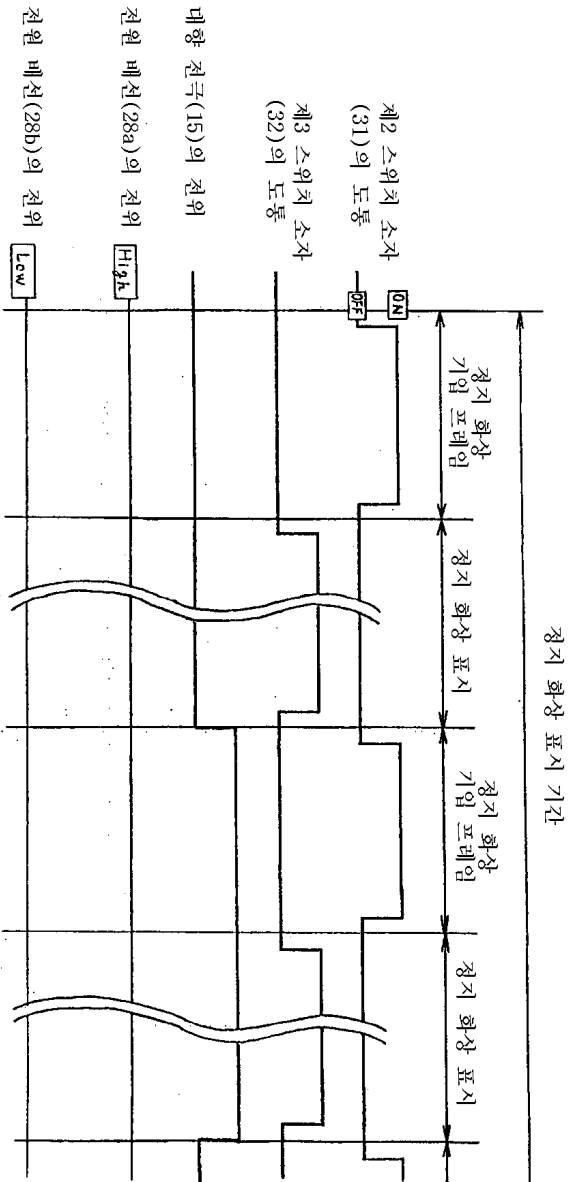


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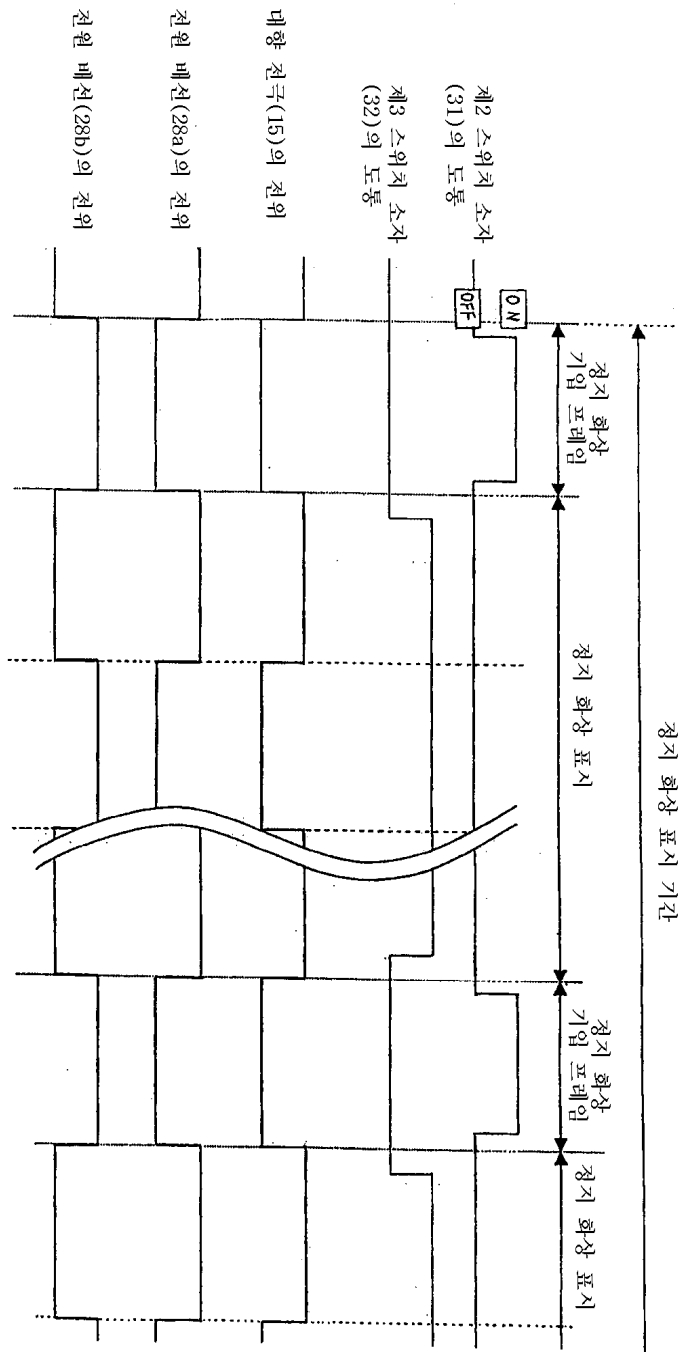


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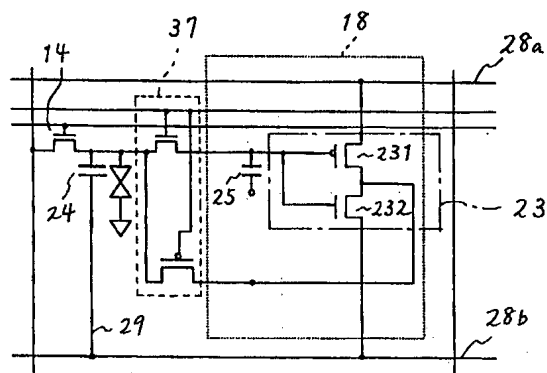


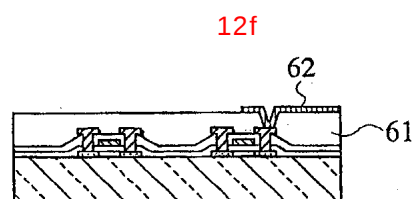
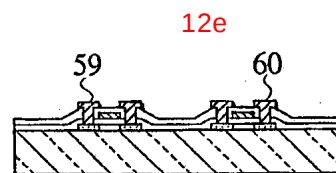
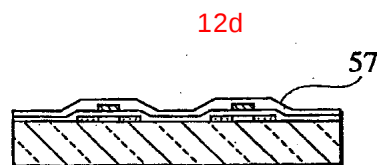
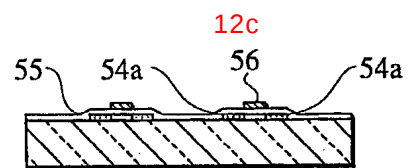
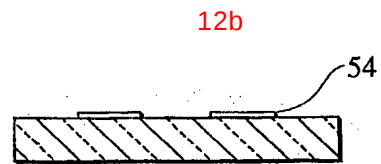
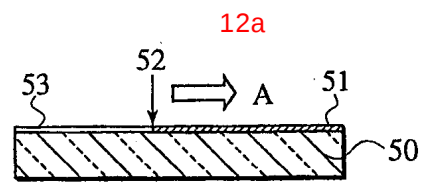
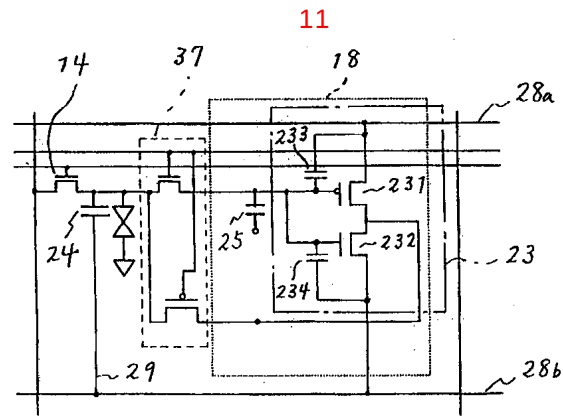


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구동 회로부 | 화소부

专利名称(译)	显示装置及其驱动方法		
公开(公告)号	KR100406454B1	公开(公告)日	2003-11-19
申请号	KR1020010075271	申请日	2001-11-30
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IPC分类号	G09G3/36		
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外部链接	Espacenet		

摘要(译)

目的：提供一种包括DM（数字存储器）单元的显示装置及其驱动方法，其实现像素的高纵横比。组成：液晶显示装置（100）由显示像素部分（110）构成，其中形成多个显示像素（10）；扫描驱动器（120）；和数据驱动器（130）。在阵列基板上，本实施例的扫描驱动器（120）和数据驱动器（130）与稍后描述的信号线（11），稍后描述的扫描线（12）和稍后描述的像素一体形成。电极（13）等。在显示像素部分（110）中，多条信号线（11）和与信号线（11）交叉的多条扫描线（12）被布置成在阵列基板上形成具有绝缘膜的矩阵（未示出）插入其间。显示像素（10）形成在两条线的交叉点处。

